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Replacement Specification

Please amend the paragraph bridging page 12 to page 13 as follows:

A plurality of permanent magnets 401 is disposed substantially on the circumference, in order to impress magnetic field around the wafer. High frequency impression to the electrode 403 by the high frequency source 404 generates plasma in the processing chamber. Magnetic field impression improves the plasma generation efficiency to enable to generate a high-density plasma. For instance, 13.56 MHz is adopted as high frequency and 120 Guass as magnetic flux density around the wafer. In the processing chamber, plasma etching, resist ashing, plasma CVD (chemical vapor deposition), sputter film deposition or other processing can be performed on the wafer.